Compound Semiconductor Materials Committee China TC Chapter
Joint Meeting Summary and Minutes

China Fall Standards Meeting 2025
October 22nd, 2025, 09:30-16:30
Qingdao, Shandong

TC Chapter Announcements

Next TC Chapter Meeting

China Spring Standards Meeting 2026

TBD, China, 2026

Table 1 Meeting Attendees

Italics indicate virtual participants

Co-Chairs: Guoyou Liu(CRRC TIMES)
SEMI Staff: Sara Ma (SEMI China),Ein Wu (SEMI China), Hailey Yan(SEMI China), Ella Jin(SEMI China)

Company	*Last*	*First*	*Company*	*Last*	*First*
CRRC TIMES	Liu	Guoyou	CRRC TIMES	Li	Chengzhan
Runxin Micro	Wang	Ronghua	Sinopatt	Zhang	Neng
Perfect Crystal	Lu	Min	TOPE	Ni	Weijiang
Linton	Hu	Dongli	Dynax	Qian	Hongtu
Linton	Peng	Yiqi	Westlake Inst	Liu	Dongli
NJU	Chen	Huabin	CETC13	Sun	Niefeng
TSSST	Li	Ruiping	*HIT*	*Gan*	*Yang*
SEMILAB	Ji	Bovey	*ZKS*	*Liu*	*Zhibin*
SEMILAB	*Márton*	*Attila*	*Japan AIST*	*Makoto*	*Kitabatake*
Vulcan	Wu	Ruixin	*SEMILAB*	*Vígh*	*Benjámin*
Hebei Synlight	Cui	Jingguang	Agilent	Song	Juane
Hwatsing	Wang	Yang	Intertek	Su	Yang
Jingyi	Zhou	Liang	Merck	Celine	Xu
AK Optics	Si	Yashan	MRSI	Zhou	Limin
TSD	He	Mingxian	Schunk Xycarb	Ye	Lun
Googol Tech	Huang	Lianzhen	WINIFRED	Li	Xiaodong
Guangdong Tianyu	Ding	Xiongjie	Epiworld	Qian	Weining
Guangdong Tianyu	Liu	Wei	TMJT	Wang	Yuanli
TÜV	Xin	Xing	Gaoce	Yu	Hongyan
TÜV	Liu	Xinling	SRI	Guo	Zheng
TÜV	Wang	Kiki	SICC	Yang	Shixing
TÜV	Li	Zemin	SICC	Zhang	Wenlong
SMEE	Pan	Jufeng	Semisic crystal	Wang	Guangyao
TÜV	Lv	Hengyong	Semisic crystal	Cui	Yating

VITAL	Su	Yu	Delta	Dong	Yuanyuan
Hwatsing	Xu	Zhenjie	Dynax	Pei	Yi
Intertek	Wang	Chen	TÜV	Yang	Shuai

Table 2 Leadership Changes

WG/TF/SC/TC Name	*Previous Leader*	*New Leader*
Compound Semiconductor Materials		
None		

Table 3 Committee Structure Changes

Previous WG/TF/SC Name	*New WG/TF/SC Name or Status Change*
Compound Semiconductor Materials	
None	

Table 4 Ballot Results

Document #	*Document Title*	*Committee Action*
Compound Semiconductor Materials		

#1 **Passed** ballots and line items will be submitted to the ISC Audit & Review Subcommittee for procedural review.

#2 **Failed** ballots and line items were returned to the originating task forces for re-work and re-balloting or abandoning.

Table 5 Activities Approved by the GCS between meetings of the TC Chapter

#	*Type*	*SC/TF/WG*	*Details*
Compound Semiconductor Materials			
None			

Table 6 Authorized Activities

Listing of all revised or new SNARF(s) approved by the Originating TC Chapter.

#	*Type*	*SC/TF/WG*	*Details*
Compound Semiconductor Materials			
	SNARF	SiC Epitaxial Wafer TF	New Standard: Test method for determining net carrier density profiles in silicon carbide epitaxial wafers by capacitance-voltage measurements with a mercury probe
	SNARF	SiC Epitaxial Wafer TF	New Standard: Specification For Bonding Silicon Carbide Homoepitaxial Wafer

#1 SNARFs and TFOFs are available for review on the SEMI Web site at:
http://downloads.semi.org/web/wstdsbal.nsf/TFOFSNARF

Table 7 Authorized Ballots

#	*When*	*TF*	*Details*
Compound Semiconductor Materials			

Table 8 SNARF(s) Granted a One-Year Extension

#	*TF*	*Title*	*Expiration Date*
Compound Semiconductor Materials			

Table 9 SNARF(s) Abolished

#	*TF*	*Title*
Compound Semiconductor Materials		
6767	Silicon Carbide Substrate Task Force	New Standard: Test Method for GBIR, SBIR, GF3R, SFQR and SORI of Silicon Carbide Wafers by Oblique Incident Interference Method
6769	Silicon Carbide Substrate Task Force	New Standard: Test Method for Residual Stress of Silicon Carbide Wafers by Photoelastic Effect

Table 10 Standard(s) to receive Inactive Status

Standard Designation	*Title*
Compound Semiconductor Materials	
None	

Table 11 New Action Items

Item #	*Assigned to*	*Details*
Compound Semiconductor Materials		
None		

Table 12 Previous Meeting Action Items

Item #	*Assigned to*	*Details*
Compound Semiconductor Materials		
None		

1 Welcome, Reminders, and Introductions

Committee co-chair Guoyou Liu chaired the meeting and welcomed all attendees including the online attendees. All the attendees introduced themselves. And agenda was reviewed.

Attachment: 2 Compound&HB-LED TC Fall Meeting 2025 Agenda.10162025

2 SEMI Staff Report

Sara Ma (SEMI China) gave the SEMI Staff Report. Of note:

Action Item:

- SEMI International Standards Overview
- SEMI Standards Publications
- 2025 &2026 Critical Dates for SEMI Standards Ballots
- NARSC Members
- Organization chart

Attachment: 3 SEMI Staff Report

3 Liaison Reports

4.1 Compound Semiconductor Materials Europe TC Chapter

Sara Ma(SEMI) reported for the Compound Semiconductor Materials Europe TC Chapter. Of note:

Action Item:

- Meeting Information
- Leadership / Leadership Changes
- Committee Structure Changes
- Organization Chart
- Ballot Results
- Task Force Highlights

Attachment: 9 EU CSM Liaison Report November 2024

4.2 Compound Semiconductor Materials Japan TC Chapter

Sara Ma (SEMI) reported for the Compound Semiconductor Materials Japan TC Chapter. Of note:

Action Item:

- Meeting Information
- Leadership
- Organization Chart
- Ballot Results
- Task Force Highlights

Attachment: 10 CSM_JA TC Chapter Liaison Report_October 2025_R1

4 Ballot Review

None

5 Subcommittee and Task Force Reports

a) *Silicon Carbide Substrate Task Force*

Min Lu (Perfect Crystal) reported for the Silicon Carbide Substrate Task Force. This report contained information on:

Action Item:

- Introduced the task force’s leaders and members.
- Documents in Development:
  - ➢ Doc.6767: New Standard: Test Method for GBIR, SBIR, GF3R, SFQR and SORI of Silicon Carbide Wafers by Oblique Incident Interference Method
  - ➢ Doc.6769: New Standard: Test Method for Residual Stress of Silicon Carbide Wafers by Photoelastic
- Specific Work
  - Based on the second global ballot of this year and the spring session on June 17, They hope to abolish the documents#6767&#6769.
  - The Task Force member Shanxi Shuoke Crystal Co., Ltd. will continue to re-apply for《Test Method for Flatness of Silicon Carbide Wafers by Optical Interference》.
  - Documents in Development: #7323——Specification of High-purity silicon carbide powder for SiC Crystal
- Extension Request
  - None

Attachment: 4 SEMI China CS Std. Technical Committee Silicon Carbide substrate Task Force – 废止说明 10092025

b) *GaN Task Force*

Yi Pei (Dynax) reported for the GaN Task Force. This report contained information on:

Action Item:

- Introduced the task force’s leaders and members.
- Documents in Development:

  #7322 Specification of Multiple Materials Substrate for GaN Epitaxial Growth aiming at HB-LED

Attachment: 6 GaN TF(1)(1)

c) *SiC Epitaxial Wafer Task Force*

Weining Qian (Epiworld) reported for the 4H-SiC Epitaxial Wafer Task Force. This report contained information on:

Action Item:

- Introduced the task force’s leaders and members.
- Progress of Documents work:
  - Doc. 6693, New Standard:Specification for 4H-SiC Homoepitaxial Wafer
    - Ballot passed and forwarded to ISC A&R
    - Document is published as SEMI M92-0423

Attachment: 8 Report of 4H-SiC epitaxial wafer task force_20251011

6 Review of Previous Meeting Minutes

The TC Chapter reviewed the minutes of the previous meeting.

Motion:	To approve the minutes of the previous meeting as written
By / 2nd:	Hongtu Qian(Dynax) / Bovey Ji(SEMILab)
Discussion:	None
Vote:	28Y - 0 N, (Total 28 companies.) Motion Passed.

Attachment: 11 China CSM&HB-LED TC Joint Spring Meeting Minutes 20250617

7 Old Business

7.1.1 SNARF(s) Abolished: #6767 New Standard: Test Method for GBIR, SBIR, GF3R, SFQR and SORI of Silicon Carbide Wafers by Oblique Incident Interference Method

Motion: Abolish the SNARF.

By / 2nd: Min Lu(Perfect Crystal) / Niefeng Sun (CETC13)

Discussion: None

Vote: 40 in favor and 0 opposed 2 abstain. (Total 42 companies.) Motion passed.

Attachment: 4 SEMI China CS Std. Technical Committee Silicon Carbide substrate Task Force - 废止说明 10092025

7.1.2 SNARF(s) Abolished: #6769 New Standard: Test Method for Residual Stress of Silicon Carbide Wafers by Photoelastic Effect

Motion: Abolish the SNARF.

By / 2nd: Min Lu(Perfect Crystal) / Niefeng Sun (CETC13)

Discussion: None

Vote: 40 in favor and 0 opposed 2 abstain. (Total 42 companies.) Motion passed.

Attachment: 4 SEMI China CS Std. Technical Committee Silicon Carbide substrate Task Force - 废止说明 10092025

8 New Business

8.1 New SNARFs

8.1.1 SNARF, New Standard: Test method for determining net carrier density profiles in silicon carbide epitaxial wafers by capacitance-voltage measurements with a mercury probe

Motion: Approve the SNARF.

By / 2nd: Bovey Ji(SEMILAB) / Ruiping Li (TSSST)

Discussion: None

Vote: 28 in favor and 0 opposed 0 abstain. (Total 28 companies.) Motion passed.

Attachment: 12 SEMI_Proposal_SiC_EPI_Dopant_Characterizatoin_By_mercury_CV_v3

8.1.2 SNARF, Specification For Bonding Silicon Carbide Homoepitaxial Wafer

Motion: Approve the SNARF.

By / 2nd: HungKit Ting（Guangdong Tianyu）/ Weijiang Ni (TOPE)

Discussion: Yashan Si (AK Optics): Do you have the requirement size of the void.

HungKit Ting（Guangdong Tianyu）:We can get the requirements from the vendors, such as millimeter or micron.

Vote: 22 in favor 4 abstain and 0 opposed (Total 26 companies.) Motion passed.

Attachment: 13 SNARF-Specification For Bonding Silicon Carbide Homoepitaxial Wafer - TYSiC

8.2 Requests for ballots

None

8.3 SNARF(s) Granted a One-Year Extension

None

8.4 Five-Year-Review

None

8.5 New Task Force

None

9 Next Meeting and Adjournment

The next meeting of the Compound Semiconductor Materials & HB-LED China TC Chapter is scheduled for TBD, 2026 in China.

For more information, please visit Standards Calendar at http://www.semi.org/en/standards

Adjournment: 16:30.

Respectfully submitted by:

Sara Ma

SEMI China

Phone: 021-6027-8578

Email: sarama@semi.org

Minutes tentatively approved by:

Jiangbo Wang (HC SEMITEK), Compound Semiconductor Materials Committee and HB-LED Committee China TC Chapter Co-chair	2025/11/10
Guoyou Liu (CRRC TIMES), Compound Semiconductor Materials Committee and HB-LED Committee China TC Chapter Co-chair	2025/11/10

Table 13 Index of Available Attachments[#1]

Title	*Title*
1 Chinese SEMI Standard Meeting Reminders	2 Compound&HB-LED TC Fall Meeting 2025 Agenda.10162025
3 SEMI Staff Report	4.SEMI China CS Std. Technical Committee Silicon Carbide substrate Task Force - 废止说明 10092025
5 Standards-silicon carbide powder-Yiqi	6 GaN TF(1)(1)
7 SNARF_Specification of Multiple Materials Substrate for GaN Epitaxial Growth aiming at HB-LED-修改版 2(1)	8 Report of 4H-SiC epitaxial wafer task force_20251011
9 EU CSM Liaison Report November 2024	10 CSM_JA TC Chapter Liaison Report_October 2025_R1
11 China CSM&HB-LED TC Joint Spring Meeting Minutes 20250617	12.SEMI_Proposal_SiC_EPI_Dopant_Characterizatoin_By_mercury_CV_v3
13 SNARF-Specification For Bonding Silicon Carbide Homoepitaxial Wafer - TYSiC	14 TEST METHOD FOR GEOMETRY OF SILLICON CARBIDE WAFERS BY SINGLE SIDE OBLIQUE INCIDENT INTERFERENCE_20251017

#1 Due to file size and delivery issues, attachments must be downloaded separately. A .zip file containing all attachments for these minutes is available at www.semi.org. For additional information or to obtain individual attachments, please contact [SEMI Staff Name] at the contact information above.